MAR 2 4 2005 TRIANSMITTAL OF FORMAL DRAWINGS

Docket No. BUR920040015US1 (17427)

In Application Of:

Matthew J. Breitwisch, et al.

Application No.	Filing Date	Confirmation No.	Examiner	Customer No.	Group Art Unit
10/710,821	August 5, 2004	6753	Unassigned	23389	2812

Invention:

ISOLATED FULLY DEPLETED SILICON-ON-INSULATOR REGIONS BY SELECTIVE ETCH

Address to:

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Transmitted herewith are:

3 sheets of formal drawing(s) for this application.

Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

Signature

Leslie S. Szivos, Ph.D. Registration No. 39,394 Dated: March 22, 2005

I certify that this document and attached formal drawings are being deposited on 03/22/05 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 223131450

Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

Typed or Printed Name of Person Mailing Correspondence